

Quarterly Reliability Monitoring Results

Quarters: Q1/2022 to Q4/2023

Based on structural similarity

| Supplier | User Part Number | |
|---------------------------|---------------------------------------------------------------------------------------------------------------------------------------------------------------|------------------------------------------------|
| Nexperia B.V. | BAS321-Q | |
| Name of Laboratory | Part Description | |
| Assembly reliability labs | Nexperia DHAM Small Signal Bipolar Diode SMD package | |
| Based on AEC-Q101 Test | Test Conditions | Duration # Lots # Quantity # Rejects |
| # E1 | TEST Pre- and Post-Stress Electrical Test Tamb = 25 °C | N/A see below all parts see below |
| # A1 | PC Preconditioning JESD22-A113 Bake Tamb = 125 °C Soak Tamb = 85 °C, RH = 85% Reflow soldering | 24 hours 168 hours 3 cycles 1514 64430 0 |
| # B1 | HTRB High Temperature Reverse Bias MIL-STD-750-1 M1038 Method A Tj = Tjmax, Vr = 100% of max. datasheet reverse voltage | 1000 hours 110 4920 0 |
| # A4 | TC Temperature Cycling JESD22-A104 -65 °C to Tjmax, not to exceed 150°C | 1000 cycles 311 14080 0 |
| # A3 or | UHAST Unbiased HAST JESD22-A118 Tamb = 130 °C, RH = 85 % | 96 hours 311 14080 0 |
| # A3 alt | AC Autoclave JESD22-A102 Tamb = 121 °C, RH = 100 % Pressure = 205 kPa (29.7 psia) | |
| # A2 alt | H3TRB High Humidity High Temperature Reverse Bias JESD22-A101 Tamb = 85 °C, RH = 85%, VR = 80 % of rated reverse voltage ^[1] | 1000 hours 311 14080 0 |
| # A5 | IOL Intermittent Operating Life MIL-STD-750 Method 1037 ton = toff, devices powered to insure ΔTj = 100 °C for 15000 cycles | 1000 hours 312 14120 0 |
| # C8 | RSH Resistance to Solder Heat JESD22-A111 260 °C ± 5 °C | 10 s 269 8070 0 |
| # C10 | SD Solderability J-STD-002 | 222 6660 0 |

[1] The maximum applied voltage is limited by test chamber set up and does not exceed 115V.

Calculation of FIT and MTTF

Test considered for FIT calculation: High Temperature Reverse Bias (HTRB, Test #B1)

Confidence level 60%, derated to 55 °C, activation energy 0.7 eV, test time 168 to 1000 hours

| Wafer Fab | Technology | Quantity | Rejects | Failure Rate (FIT) | MTTF (hrs) |
|------------------|----------------------------|----------|---------|--------------------|------------|
| Nexperia DHAM | Small Signal Bipolar Diode | 4920 | 0 | 0,86 | 1,16E+09 |

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